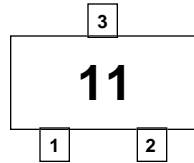
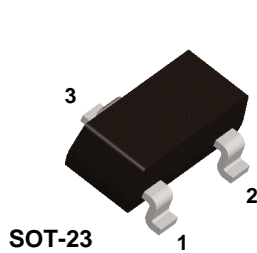
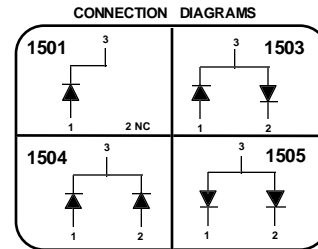


MMBD1501/A / 1503/A / 1504/A / 1505/A



MARKING

MMBD1501	11	MMBD1501A	A11
MMBD1503	13	MMBD1503A	A13
MMBD1504	14	MMBD1504A	A14
MMBD1505	15	MMBD1505A	A15



High Conductance Low Leakage Diode

Sourced from Process 1L.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W_{IV}	Working Inverse Voltage	180	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	600	mA
i_f	Recurrent Peak Forward Current	700	mA
$i_{f(surge)}$	Peak Forward Surge Current	1.0	A
	Pulse width = 1.0 second	2.0	A
	Pulse width = 1.0 microsecond		
T_{stg}	Storage Temperature Range	-55 to +150	°C
T_J	Operating Junction Temperature	150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMBD1501/A/ 1503-1505/A*	
P_D	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

*Device mounted on glass epoxy PCB 1.6" X 1.6" X 0.06"; mounting pad for the collector lead min. 0.93 in²

High Conductance Low Leakage Diode

(continued)

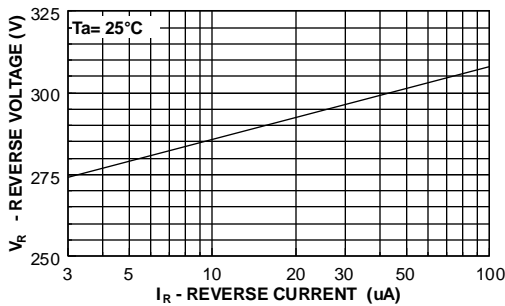
Electrical Characteristics

TA = 25°C unless otherwise noted

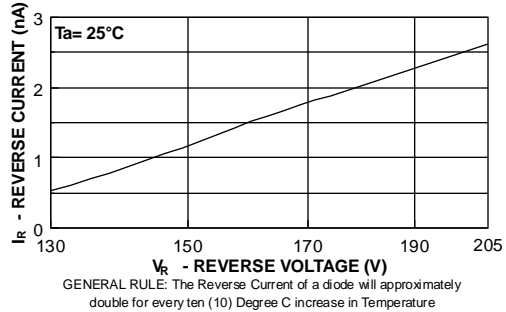
Symbol	Parameter	Test Conditions	Min	Max	Units
B_V	Breakdown Voltage	$I_R = 5.0 \mu A$	200		V
I_R	Reverse Current	$V_R = 125 V$ $V_R = 125 V, T_A = 150^\circ C$ $V_R = 180 V$ $V_R = 180 V, T_A = 150^\circ C$		1.0 3.0 10 5.0	nA μA nA μA
V_F	Forward Voltage	$I_F = 1.0 mA$ $I_F = 10 mA$ $I_F = 50 mA$ $I_F = 100 mA$ $I_F = 200 mA$ $I_F = 300 mA$	620 720 800 830 0.87 0.9	720 830 890 930 1.1 1.15	mV mV mV mV V V
C_O	Diode Capacitance	$V_R = 0, f = 1.0 MHz$		4.0	pF

Typical Characteristics

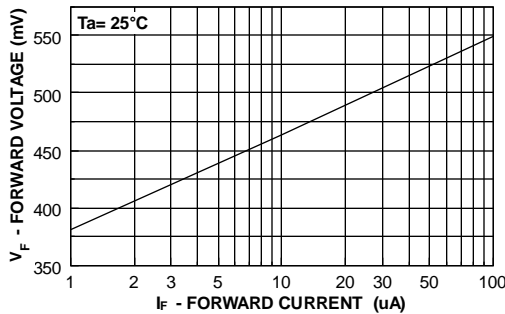
REVERSE VOLTAGE vs REVERSE CURRENT
BV - 3.0 to 100 μA



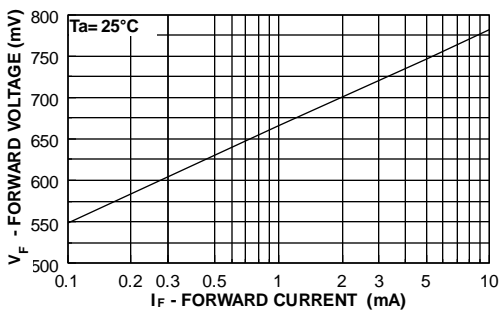
REVERSE CURRENT vs REVERSE VOLTAGE
IR - 130 - 205 Volts



FORWARD VOLTAGE vs FORWARD CURRENT
VF - 1 to 100 μA



FORWARD VOLTAGE vs FORWARD CURRENT
VF - 0.1 to 10 mA



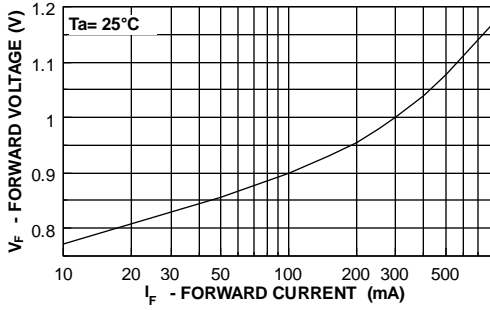
MMBD1501/A / 1503/A / 1504/A / 1505/A

High Conductance Low Leakage Diode

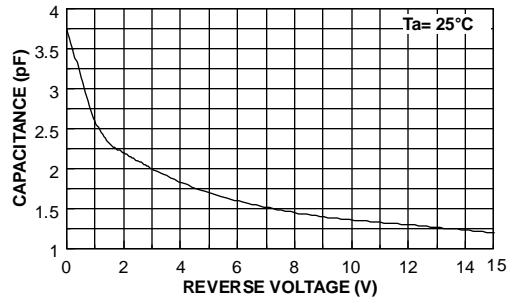
(continued)

Typical Characteristics (continued)

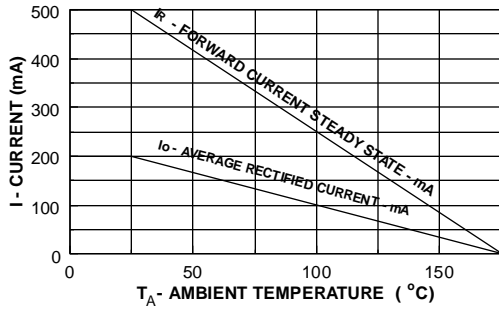
FORWARD VOLTAGE vs FORWARD CURRENT
 V_F - 10 to 800 mA



CAPACITANCE vs REVERSE VOLTAGE
 V_R - 0 to 15 V



Average Rectified Current (I_o) & Forward Current (I_F) versus Ambient Temperature (T_A)



POWER DERATING CURVE

